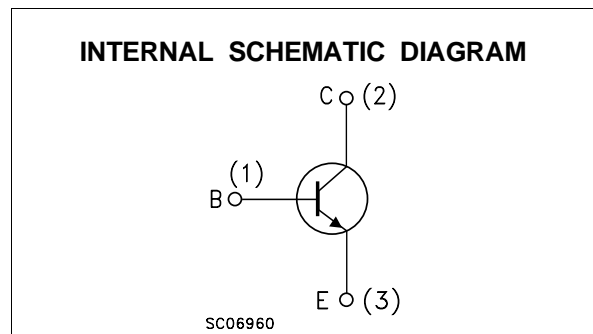
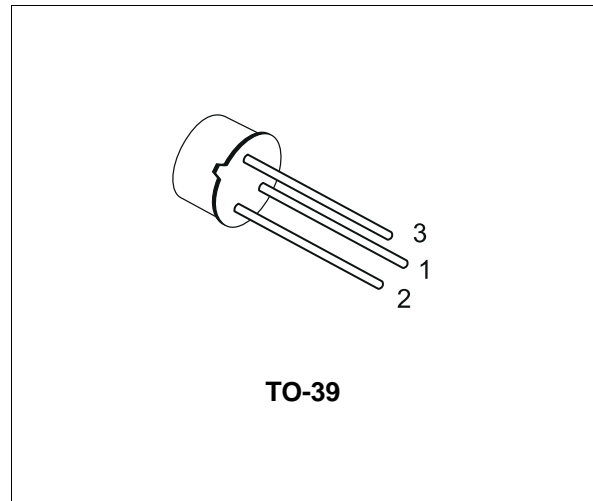


EPITAXIAL PLANAR NPN

DESCRIPTION

The 2N1711 is a silicon Planar Epitaxial NPN transistor in Jedec TO-39 metal case. It is intended for use in high performance amplifier, oscillator and switching circuits.

The 2N1711 is also used to advantage in amplifiers where low noise is an important factor.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	75	V
V_{CER}	Collector-Emitter Voltage ($R_{BE} \leq 10\Omega$)	50	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	500	mA
P_{tot}	Total Dissipation at $T_{amb} \leq 25^\circ C$	0.8	W
	at $T_C \leq 25^\circ C$	3	W
	at $T_C \leq 100^\circ C$	1.7	W
T_{stg}	Storage Temperature	-65 to 175	$^\circ C$
T_j	Max. Operating Junction Temperature	175	$^\circ C$

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-Case	Max	50	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	187.5	$^{\circ}C/W$

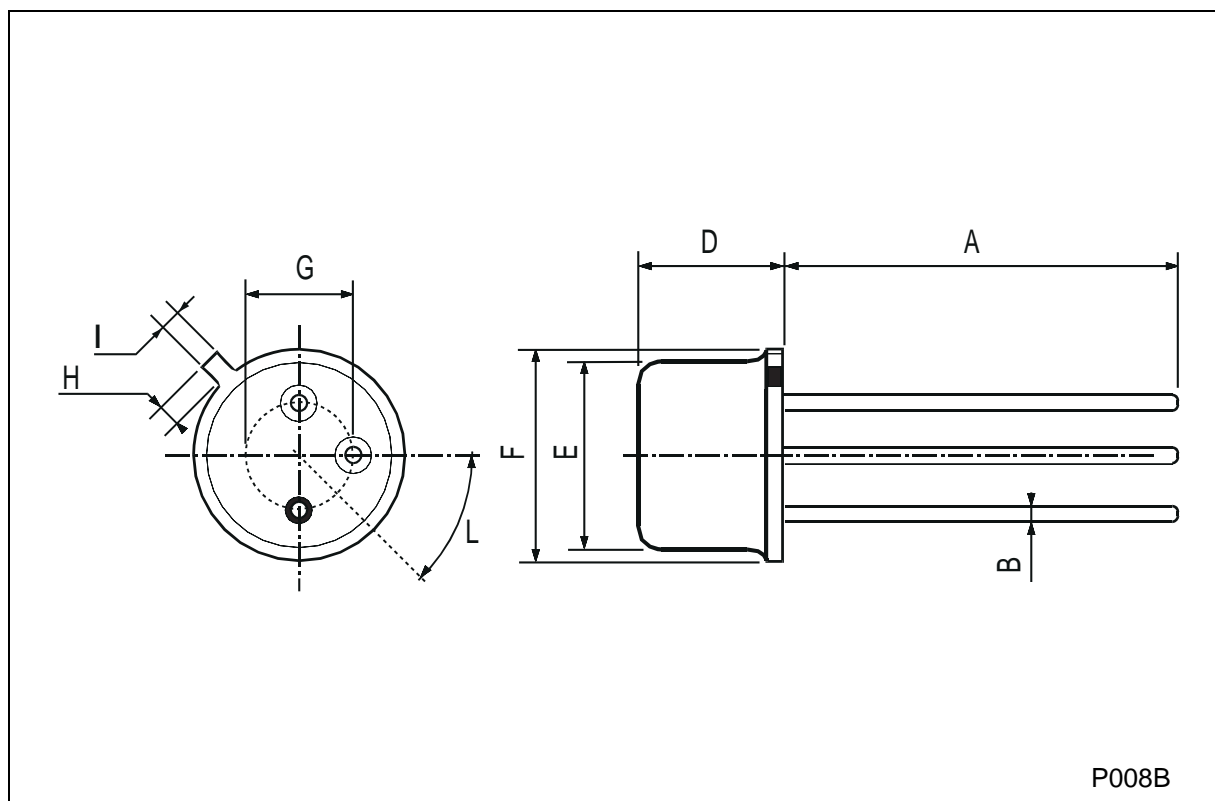
ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = 60 V$ $V_{CB} = 60 V \quad T_C = 150^{\circ}C$			10 10	nA μA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5 V$			5	nA
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_E = 0$)	$I_C = 100 \mu A$	75			V
$V_{(BR)CER}^*$	Collector-Emitter Breakdown Voltage ($R_{BE} \leq 10\Omega$)	$I_C = 10 mA$	50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = 100 \mu A$	7			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 150 mA \quad I_B = 15 mA$		0.5	1.5	V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 150 mA \quad I_B = 15 mA$		0.95	1.3	V
h_{FE}^*	DC Current Gain	$I_C = 10 \mu A \quad V_{CE} = 10 V$ $I_C = 0.1 mA \quad V_{CE} = 10 V$ $I_C = 10 mA \quad V_{CE} = 10 V$ $I_C = 150 mA \quad V_{CE} = 10 V$ $I_C = 500 mA \quad V_{CE} = 10 V$ $I_C = 10 mA \quad V_{CE} = 10 V$ $T_C = -55^{\circ}C$	20 35 75 100 40 35	60 80 130 130 75 65	300	
h_{fe}	Small Signal Current Gain	$I_C = 1 mA \quad V_{CE} = 10 V \quad f = 1 KHz$	70	135	300	
f_T	Transition Frequency	$I_C = 50 mA \quad V_{CE} = 10 V \quad f = 20 MHz$	70	100		MHz
C_{EBO}	Emitter-Base Capacitance	$I_C = 0 \quad V_{EB} = 0.5 V \quad f = 1 MHz$		50	80	pF
C_{CBO}	Collector-Base Capacitance	$I_E = 0 \quad V_{CB} = 10 V \quad f = 1 MHz$		18	25	pF
NF	Noise Figure	$I_C = 0.3 mA \quad V_{CE} = 10 V$ $R_g = 510 \Omega \quad f = 1 KHz$		3.5	8	dB
h_{ie}	Input Impedance	$I_C = 1 mA \quad V_{CE} = 5 V \quad f = 1 KHz$		4.4		K Ω
h_{re}	Reverse Voltage Ratio	$I_C = 1 mA \quad V_{CE} = 5 V \quad f = 1 KHz$		7.3×10^{-4}		
h_{oe}	Output Admittance	$I_C = 1 mA \quad V_{CE} = 5 V \quad f = 1 KHz$		23.8		μS

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 1\%$

TO-39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



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